

## MOS/FET/P-CHANNEL, ENHANCEMENT, SINGLE

TYPE	PACKAGE	BV <sub>DSS</sub> Volts Min.	I <sub>GSS</sub> Max.	I <sub>DSS</sub> nA Max.	BV <sub>GSS</sub> Transient	V <sub>GS(TH)</sub>		r <sub>DS(on)</sub> Ohms Max.(2)	y <sub>fs</sub> μmho		C <sub>iss</sub> pf Max.	C <sub>rss</sub> pf Max.	NF Typ. dB
						Volts Min.	Volts Max.		Min.	Max.			
3N163	TO-72	-40	(1)	0.2	±125	-2.0	-5.0	250	2000	4000	2.5	0.7	1.0
3N164	TO-72	-30	(1)	0.4	±125	-2.0	-5.0	300	1000	4000	2.5	0.7	1.0
3N172	TO-72	-40	0.2nA	0.4	-40(3)	-2.0	-5.0	250	1500	4000	3.5	1.0	1.0
3N173	TO-72	-30	0.5nA	10.0	-30(3)	-2.0	-5.0	350	1000	4000	3.5	1.0	1.0
UC1764	TO-72	-30	(1)	10.0	±125	-2.0	-5.0	300	1000	4000	3.0	1.0	2.0

- (1) Dependent upon package leakage which is guaranteed to be below 10pA.  
 (2) Measured at V<sub>GS</sub> = -20V.  
 (3) Integrated zener protected gates.

## DUAL MOS/FET/P-CHANNEL, ENHANCEMENT

TYPE	PACKAGE	V <sub>T1-2</sub> mV Max.	ΔV <sub>GS</sub> μV/°C Max.	BV <sub>DSS</sub> Volts Min.	I <sub>DSS</sub> nA Max.	C <sub>rss</sub> pf Max.	r <sub>DS(on)</sub> Max. Ohms	I <sub>GSS</sub>
3N165	TO-99	100	100	-40	0.2	0.7	300(2)	(1)
3N166	TO-99	—	—	-40	0.2	0.7	300(2)	(1)
UC2766	TO-99	—	—	-30	10.0	1.0	300(2)	(1)

- (1) Dependent upon package leakage which is guaranteed to be below 10 pA. (2) Measured @ V<sub>GS</sub> = -20V.

TO99

